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SIST EN 62276:2013

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Enokristalne rezine za površinske zvočnovalovne naprave (SAW) - Specifikacija in merilna metoda

Single crystal wafers for surface acoustic wave (SAW) devices applications - Specifications and measuring method

Einkristall-Wafer für Oberflächenwellen-(OFW-)Bauelemente - Festlegungen und Messverfahren

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English version

Single crystal wafers for surface acoustic wave (SAW) device applications - Specifications and measuring methods
(IEC 62276:2012)

Tranches monocristallines pour applications utilisant des dispositifs à ondes acoustiques de surface (OAS) - Spécifications et méthodes de mesure
(CEI 62276:2012)

Einkristall-Wafer für Oberflächenwellen-(OFW-)Bauelemente - Festlegungen und Messverfahren
(IEC 62276:2012)

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Foreword

The text of document 49/1005/FDIS, future edition 2 of IEC 62276, prepared by IEC TC 49, "Piezoelectric, dielectric and electrostatic devices and associated materials for frequency control, selection and detection", was submitted to the IEC-CENELEC parallel vote and approved by CENELEC as EN 62276:2013.

The following dates are fixed:

• latest date by which the document has to be implemented at national level by publication of an identical national standard or by endorsement	(dop)	2013-08-23
• latest date by which the national standards conflicting with the document have to be withdrawn	(dow)	2015-11-23

This document supersedes EN 62276:2005.

EN 62276:2013 includes the following significant technical changes with respect to EN 62276:2005:

– terms and definitions are rearranged in accordance with the alphabetical order;

– “reduced LN” is appended to terms and definitions;

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– “reduced LT” is appended to terms and definitions;

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IEC 60862-1	NOTE Harmonized as EN 60862-1.
IEC 60862-2	NOTE Harmonized as EN 60862-2.
IEC 60862-3	NOTE Harmonized as EN 60862-3.
IEC 61019-1	NOTE Harmonized as EN 61019-1.
IEC 61019-2	NOTE Harmonized as EN 61019-2.
ISO 4287	NOTE Harmonized as EN ISO 4287.

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Annex ZA
(normative)

Normative references to international publications with their corresponding European publications

The following documents, in whole or in part, are normatively referenced in this document and are indispensable for its application. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

NOTE When an international publication has been modified by common modifications, indicated by (mod), the relevant EN/HD applies.

Publication	Year	Title	EN/HD	Year
IEC 60410	1973	Sampling plans and procedures for inspection by attributes	-	-
IEC 60758	2008	Synthetic quartz crystal - Specifications and guidelines for use	EN 60758	2009

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SINGLE CRYSTAL WAFERS FOR SURFACE ACOUSTIC WAVE (SAW) DEVICE APPLICATIONS – SPECIFICATIONS AND MEASURING METHODS

FOREWORD

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This second edition cancels and replaces the first edition of IEC 62276 published in 2005. This second edition constitutes a technical revision.

This edition includes the following significant technical changes with respect to the previous edition:

– terms and definitions are rearranged in accordance with the alphabetical order;
– "reduced LN" is appended to terms and definitions;
– "reduced LT" is appended to terms and definitions;
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Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

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INTRODUCTION

A variety of piezoelectric materials are used for surface acoustic wave (SAW) filter and resonator applications. Prior to the 1996 Rotterdam IEC TC 49 meeting, wafer specifications were typically negotiated between users and suppliers. During the meeting, a proposal was announced to address wafer standardization. This standard has been prepared in order to provide industry standard technical specifications for manufacturing piezoelectric single crystal wafers to be used in surface acoustic wave devices.

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